

SANYO	No.4719	2SA1864
		PNP Epitaxial Planar Silicon Transistor

Muting Circuits, Driver Applications

Features

- On-chip bias resistors (R1 = 4.7kΩ, R2 = 4.7kΩ).
- Very small-sized package making 2SA1864-applied sets small and slim.
- Small ON resistance.
- High gain-bandwidth product f_T .

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V_{CB0}	-15	V
Collector-to-Emitter Voltage	V_{CEO}	-15	V
Emitter-to-Base Voltage	V_{EBO}	-10	V
Input Voltage	V_{IN}	-14	V
Collector Current	I_C	-100	mA
Collector Current (Pulse)	I_{CP}	-200	mA
Base Current	I_B	-20	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

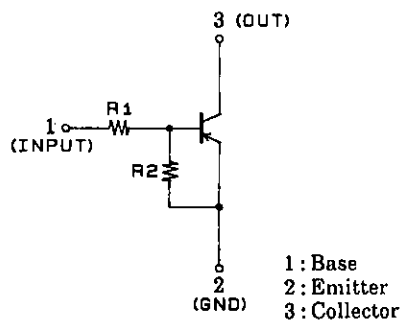
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -10V, I_E = 0$			-0.1	μA
Collector Cutoff Current	I_{CEO}	$V_{CE} = -10V, I_B = 0$			-0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-410	-532	-760	μA
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -20mA$	50			
Gain-Bandwidth Product	f_T *	$V_{CE} = -5V, I_C = -10mA$		600		MHz
Output Capacitance	C_{ob} *	$V_{CB} = -10V, f = 1MHz$		0.9		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -5mA, I_B = -0.5mA$	-30	-100		mV
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10μA, I_E = 0$	-15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = ∞$	-15			V
Input OFF-State Voltage	$V_{IN(off)}$	$V_{CE} = -2V, I_C = -100μA$	-0.8	-1.2	-1.5	V
Input ON-State Voltage	$V_{IN(on)}$	$V_{CE} = -0.3V, I_C = -20mA$	-1.0	-2.1	-4.0	V
Input Resistance	R1		3.3	4.7	6.1	kΩ
Resistance Ratio	R1/R2		0.9	1.0	1.1	
ON Resistance	R_{on}	$V_{IN} = -5V, f = 1MHz$	5.0			Ω

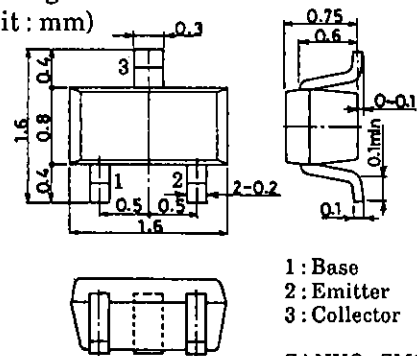
* : Characteristic of the constituent transistor.

Marking: AA

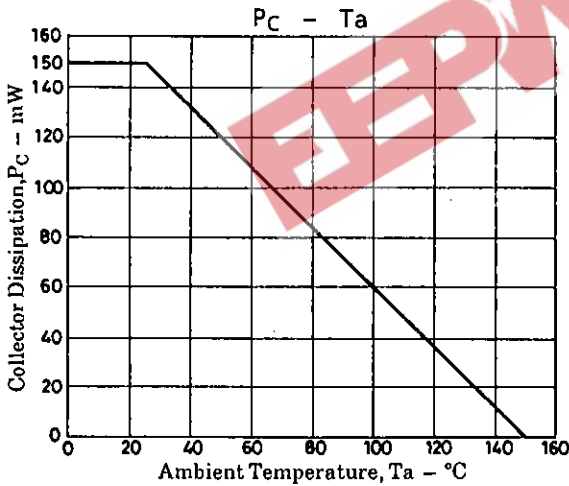
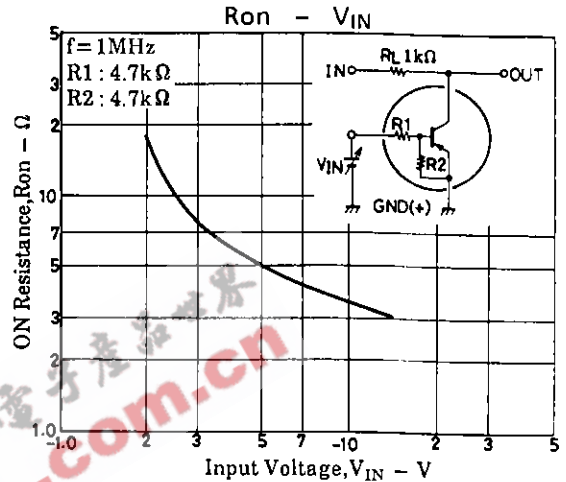
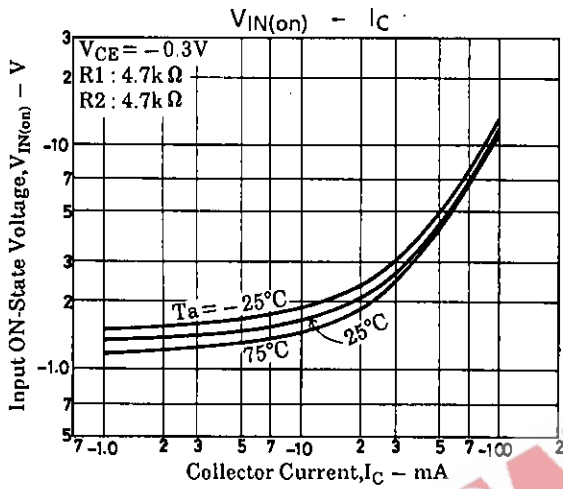
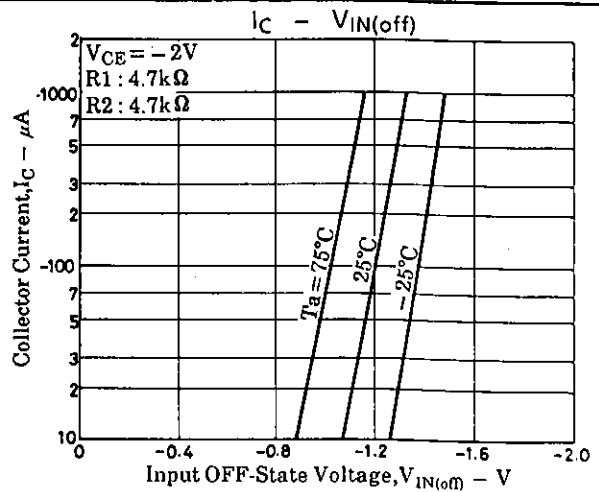
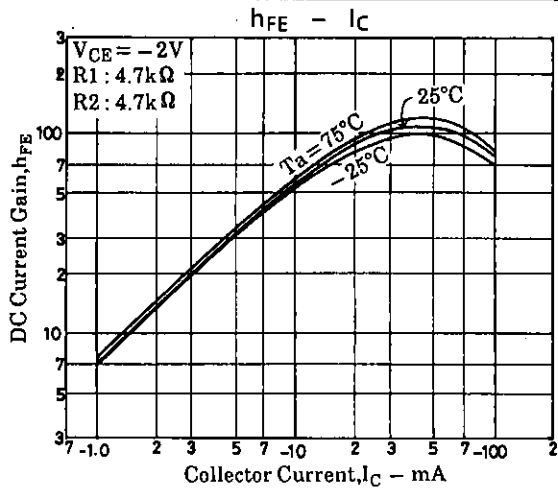
Electrical Connection



Package Dimensions 2106A
(unit: mm)



SANYO : SMCP



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